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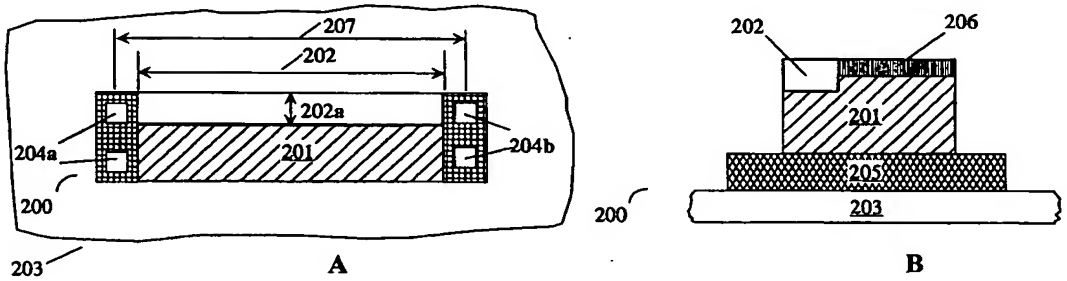
(54) Title: POLY-SILICON STRINGER FUSE



(57) Abstract: A polysilicon silicide stringer fuse is constructed having a narrow width by using an overlay tolerance of the photo stepper tool instead of the minimum critical dimension tolerance of the stepper tool. In an example embodiment, a fuse (200) for integration within a semiconductor comprises depositing an insulating layer (205) adjacent to the semiconductor substrate (203). A silicon layer (201) is formed with a first silicon material having a first resistance deposited adjacent the insulating layer (205). The silicon layer has a first width. A metal silicide stringer (202), having a second resistance different from the first resistance is deposited over a portion of the first silicon material (201) and having a second width that is less than the first width within at least a portion thereof. The metal silicide conducts current therethrough with approximately the second resistance and agglomerates in response to a programming current other than the conduct current therethrough with a same second resistance.

WO 2004/055893 A1